

IN THE ABSTRACT

Please delete the abstract and substitute the following new abstract:

-- A process of manufacturing a semiconductor device. The initial process steps are forming a first insulating film above a semiconductor substrate and removing a selected portion of the first insulating film to form an opening. The next step is depositing a first electrode, a dielectric film and a second electrode successively on a bottom portion of the opening, The deposits being oriented such that they are in substantially parallel relationship with a surface of the semiconductor substrate. The final steps are removing selected portions of the first electrode, the dielectric film and the second electrode, forming a capacitor at a selected position in the opening, forming a second insulating film at least in the opening, and forming a third insulating film on the second insulating film.--

IN THE TITLE

Please delete the title and substitute the following new title:

--MIM CAPACITOR WITH DIFFUSION BARRIER--